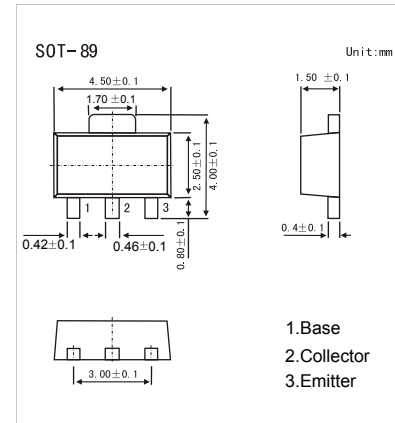


NPN Transistors

PXT2222A (KXT2222A)

■ Features

- Epitaxial planar die construction
- Complementary to PXT2907A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	75	V
Collector - Emitter Voltage	V _{CE0}	40	
Emitter - Base Voltage	V _{EB0}	6	
Collector Current - Continuous	I _C	600	mA
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	75			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = 10 mA, I _B = 0	40			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 60 V, I _E = 0			50	nA
Emitter cut-off current	I _{EB0}	V _{EB} = 5 V, I _C = 0			50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500 mA, I _B =50mA			1	V
		I _C =500 mA, I _B =15mA			0.3	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =500 mA, I _B =50mA			2	
		I _C =500 mA, I _B =15mA		0.6	1.2	
	h _{FE(1)}	V _{CE} = 10V, I _C = 0.1mA	50			
	h _{FE(2)}	V _{CE} = 10V, I _C = 10mA	75			
	h _{FE(3)}	V _{CE} = 10V, I _C = 150mA	100		300	
	h _{FE(4)}	V _{CE} = 1V, I _C = 150mA	50			
	h _{FE(5)}	V _{CE} = 10V, I _C = 500mA	40			
Delay time	t _d	V _{CC} =30V, I _C =150mA			10	ns
Rise time	t _r	V _{BE(off)} =0.5V, I _{B1} =15mA			25	
Storage time	t _s	V _{CC} =30V, I _C =150mA			225	
Fall time	t _f	I _{B1} =- I _{B2} = 15mA			60	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz			8	pF
Transition frequency	f _T	V _{CE} = 10V, I _C = 20mA, f=100MHz	300			MHz

■ Marking

Marking	*1P

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PXT2222A (KXT2222A)

■ Typical Characteristics

